



**CHENMKO ENTERPRISE CO.,LTD**

*Halogens free devices*

**SURFACE MOUNT  
PNP Silicon Power Transistor**

VOLTAGE 100 Volts CURRENT 3 Ampere

**CHT32CZGP**

**APPLICATION**

- \* Telephony and professional communication equipment.
- \* Other switching applications.

**FEATURE**

- \* Small flat package. ( SC-73/SOT-223 )
- \* Suitable for high packing density.
- \* High saturation current capability.

**CONSTRUCTION**

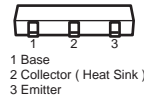
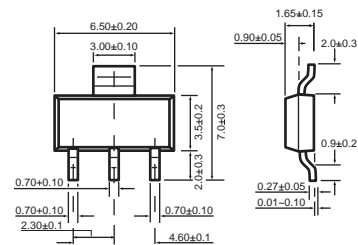
- \* PNP SILICON Transistor

**MARKING**

ZAP



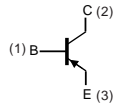
**SC-73/SOT-223**



Dimensions in millimeters

**SC-73/SOT-223**

**CIRCUIT**



**MAXIMUM RATINGS** ( At  $T_A = 25^\circ\text{C}$  unless otherwise noted )

RATINGS	CONDITION	SYMBOL	MIN.	MAX.	UNITS
Collector - Base Voltage		$V_{CB}$	-100	-	Volts
Collector - Emitter Voltage	Open Base	$V_{CEO}$	-100	-	Volts
Emitter - Base Voltage	Open Collector	$V_{EBO}$	-5	-	Volts
Collector Current DC		$I_C$	-	-3	Amps
Peak Collector Current		$I_{CM}$	-	-6	Amps
Base Current		$I_B$	-	-1	Amps
Total Power Dissipation	$T_A \leq 25^\circ\text{C}$ ; Note 1	$P_{TOT}$	-	2.0	W
Storage Temperature		$T_{STG}$	-65	+150	$^\circ\text{C}$
Junction Temperature		$T_J$	-65	+150	$^\circ\text{C}$
Operating Ambient Temperature		$T_{AMB}$	-65	+150	$^\circ\text{C}$

**Note**

1. Transistor mounted on printed-circuit board, Mounting pad for collector 10 mm<sup>2</sup>.

## RATING CHARACTERISTIC CURVES ( CHT32CZGP )

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	62.5	K/W

### CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$V_{CB}=-100V, I_E=0$	–	-200	$\mu\text{A}$
$I_{CEO}$	Base cut-off current	$V_{CE}=-60V, I_B=0$	–	-300	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$V_{EB}=-5V, I_C=0$	–	-1	mA
$h_{FE}$	DC current gain	$V_{CE}=-4V, I_C=-1A$ Note.1	25	–	
		$V_{CE}=-4V, I_C=-3A$ Note.1	10	100	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C=-3.0A, I_B=-375mA$ Note.1	–	-1.2	V
$V_{BE(ON)}$	base-emitter saturation voltage	$V_{CE}=-4V, I_C=-3A$ Note.1	–	-1.8	V
$f_T$	transition frequency	$I_C = 500\text{ mA}; V_{CE} = -10V; f = 1.0\text{ MHz}$	3	–	MHz

**Note :**

1. Pulse , 2%D.C.